

# The properties of Schottky barrier structures with metal-tunnel transparent dielectric $p\text{-Cd}_x\text{Hg}_{1-x}\text{Te}$

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*Potential barriers in Schottky diodes with metal-tunnel transparent dielectric based on  $\text{Cd}_x\text{Hg}_{1-x}\text{Te}$  with  $x \sim 0,2$ , have been studied. We used In, Tn, Mo, Al and Cr as metal barriers. Superthin dielectric,  $\text{Al}_2\text{O}_3$  and fluorine plasma films were coated between surface of  $\text{Cd}_x\text{Hg}_{1-x}\text{Te}$  and metal.*

## Л и т е р а т у р а

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